

NCE N-Channel Enhancement Mode Power MOSFET



The NCE4060I uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

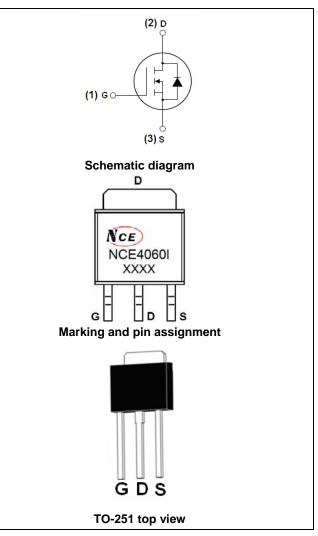
- V_{DS} =40V,I_D =60A
 R_{DS(ON)} <12mΩ @ V_{GS}=10V (Typ. 7.3 mΩ)
 R_{DS(ON)} <18mΩ @ V_{GS}=4.5V (Typ. 15 mΩ)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



Package Marking and Ordering Information

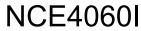
Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE4060I	NCE4060I	TO-251	-	-	-

Absolute Maximum Ratings (T_c=25[°]Cunless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	40	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι _D	60	А
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	42	А
Pulsed Drain Current	I _{DM}	200	А
Maximum Power Dissipation	PD	65	W
Derating factor		0.43	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	400	mJ
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 175	°C







Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{ejc}	2.3	°C /W	
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Electrical Characteristics (T_C=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	40	45	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	1.2	1.6	2.5	V
Desia Osuma Oz Otata Dasistanas	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	7.3	13	mΩ
Drain-Source On-State Resistance		V _{GS} =4.5V, I _D =20A	-	15	18	
Forward Transconductance	g fs	V _{DS} =10V,I _D =20A	15	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}		-	1800	-	PF
Output Capacitance	Coss	V _{DS} =20V,V _{GS} =0V, F=1.0MHz	-	280	-	PF
Reverse Transfer Capacitance	C _{rss}		-	190	-	PF
Switching Characteristics (Note 4)	·					
Turn-on Delay Time	t _{d(on)}		-	6.4	-	nS
Turn-on Rise Time	tr	V_{DD} =20V, I_D =2A, R_L =1 Ω	-	17.2	-	nS
Turn-Off Delay Time	t _{d(off)}	V _{GS} =10V,R _G =3Ω	-	29.6	-	nS
Turn-Off Fall Time	t _f		-	16.8	-	nS
Total Gate Charge	Qg	N/ 00X/L 00A	-	29		nC
Gate-Source Charge	Q _{gs}	V _{DS} =20V,I _D =20A, V _{GS} =10V	-	4.5		nC
Gate-Drain Charge	Q _{gd}	v _{GS} -10v	-	6.4		nC
Drain-Source Diode Characteristics	·		•			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =20A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	60	Α
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 20A	-	29	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	26	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

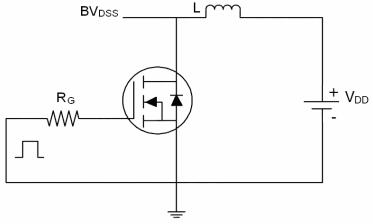
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. E_{AS} condition : Tj=25 $^\circ\!\mathrm{C}$, V_{DD} =20V, V_G =10V, L=1mH, Rg=25\Omega ,



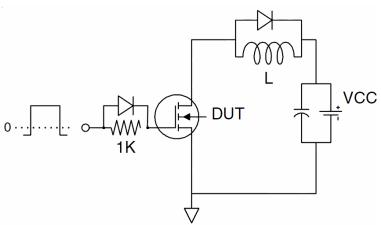
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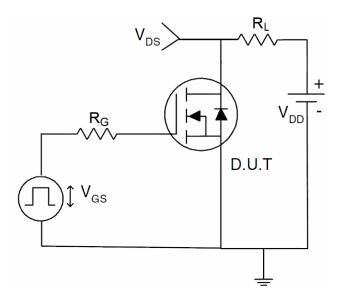
Test circuit 1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit







20

25°C

0.8

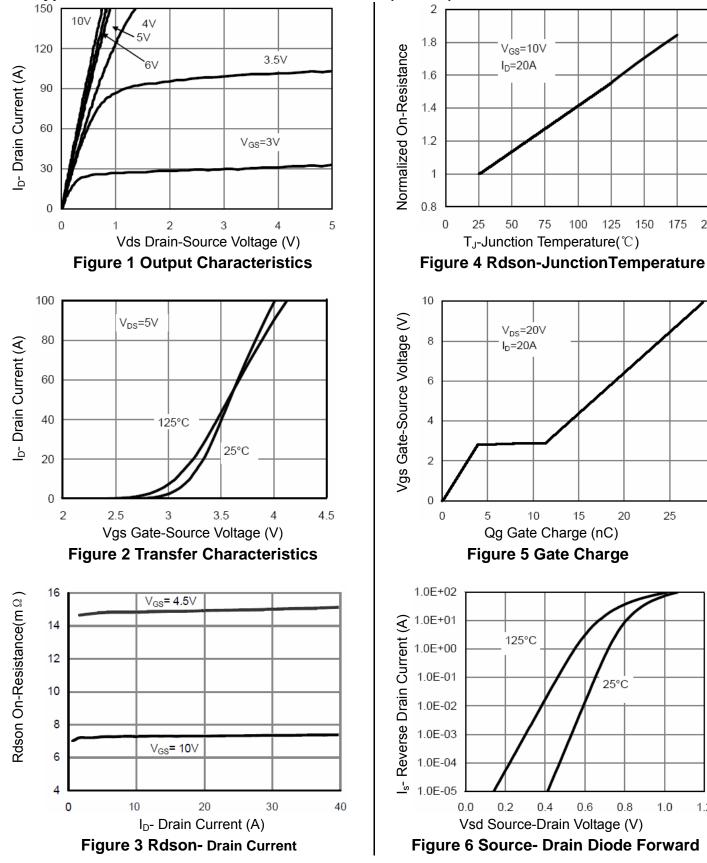
1.0

25

30

200

Typical Electrical and Thermal Characteristics (Curves)



1.2



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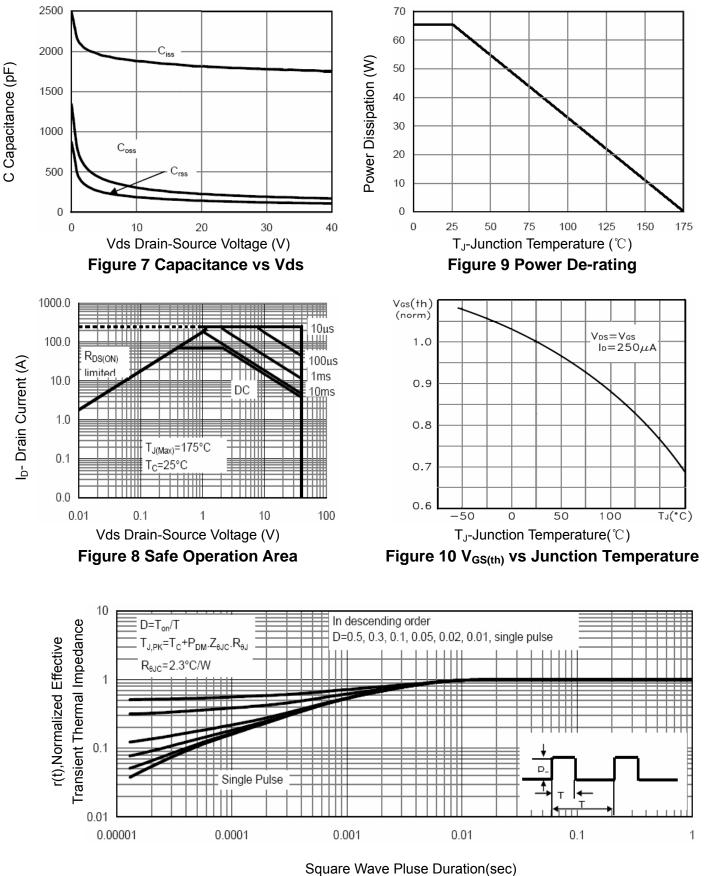


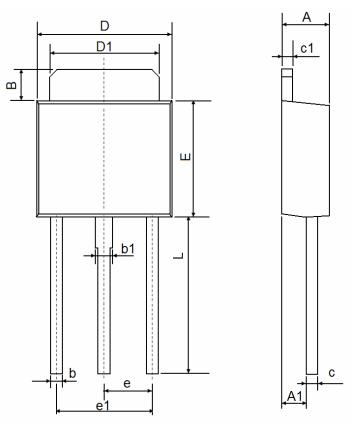
Figure 11 Normalized Maximum Transient Thermal Impedance



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TO-251 Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
A	2.200	2.400	0.087	0.094	
A1	1.050	1.350	0.042	0.054	
В	1.350	1.650	0.053	0.065	
b	0.500	0.700	0.020	0.028	
b1	0.700	0.900	0.028	0.035	
С	0.430	0.580	0.017	0.023	
c1	0.430	0.580	0.017	0.023	
D	6.350	6.650	0.250	0.262	
D1	5.200	5.400	0.205	0.213	
E	5.400	5.700	0.213	0.224	
е	2.300 TYP		0.091	ТҮР	
e1	4.500	4.700	0.177	0.185	
L	7.500	7.900	0.295	0.311	





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